

## 40V N-Channel NexFET™ Power MOSFETs

Check for Samples: [CSD18501Q5A](#)

### FEATURES

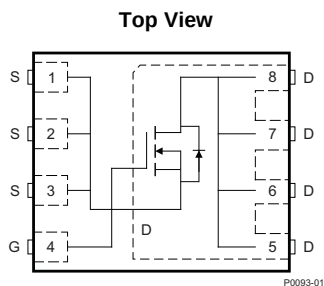
- Ultralow  $Q_g$  and  $Q_{gd}$
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

### APPLICATIONS

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Battery Motor Control

### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.



### PRODUCT SUMMARY

| Typical Values at 25°C unless otherwise stated |                               | TYPICAL VALUE   | UNIT   |
|------------------------------------------------|-------------------------------|-----------------|--------|
| $V_{DS}$                                       | Drain to Source Voltage       | 40              | V      |
| $Q_g$                                          | Gate Charge Total (4.5V)      | 20              | nC     |
| $Q_{gd}$                                       | Gate Charge Gate to Drain     | 5.9             | nC     |
| $R_{DS(on)}$                                   | Drain to Source On Resistance | $V_{GS} = 4.5V$ | 3.3 mΩ |
|                                                |                               | $V_{GS} = 10V$  | 2.5 mΩ |
| $V_{GS(th)}$                                   | Threshold Voltage             | 1.8             | V      |

### ORDERING INFORMATION

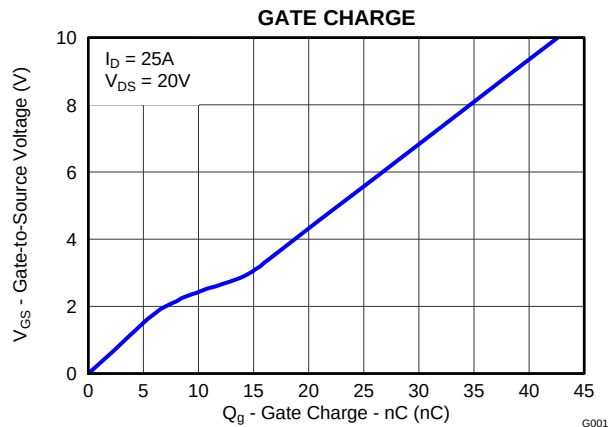
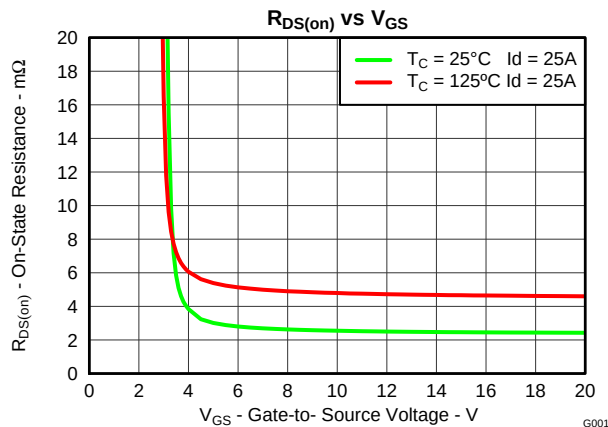
| Device      | Package                         | Media        | Qty  | Ship          |
|-------------|---------------------------------|--------------|------|---------------|
| CSD18501Q5A | SON 5-mm × 6-mm Plastic Package | 13-Inch Reel | 2500 | Tape and Reel |

### ABSOLUTE MAXIMUM RATINGS

| $T_A = 25^\circ\text{C}$ unless otherwise stated |                                                                             | VALUE      | UNIT |
|--------------------------------------------------|-----------------------------------------------------------------------------|------------|------|
| $V_{DS}$                                         | Drain to Source Voltage                                                     | 40         | V    |
| $V_{GS}$                                         | Gate to Source Voltage                                                      | ±20        | V    |
| $I_D$                                            | Continuous Drain Current (Package limited), $T_C = 25^\circ\text{C}$        | 100        | A    |
|                                                  | Continuous Drain Current (Silicon limited), $T_C = 25^\circ\text{C}$        | 155        | A    |
|                                                  | Continuous Drain Current, $T_A = 25^\circ\text{C}^{(1)}$                    | 22         | A    |
| $I_{DM}$                                         | Pulsed Drain Current, $T_A = 25^\circ\text{C}^{(2)}$                        | 142        | A    |
| $P_D$                                            | Power Dissipation <sup>(1)</sup>                                            | 3.1        | W    |
| $T_J$ , $T_{STG}$                                | Operating Junction and Storage Temperature Range                            | –55 to 150 | °C   |
| $E_{AS}$                                         | Avalanche Energy, Single Pulse $I_D = 68A$ , $L = 0.1mH$ , $R_G = 25\Omega$ | 231        | mJ   |

(1) Typical  $R_{\theta JA} = 40^\circ\text{C/W}$  on a 1-inch<sup>2</sup>, 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.

(2) Pulse duration ≤300μs, duty cycle ≤2%



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

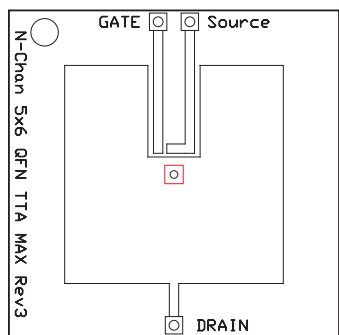
| PARAMETER               |                                  | TEST CONDITIONS                                                                            | MIN  | TYP | MAX | UNIT |    |
|-------------------------|----------------------------------|--------------------------------------------------------------------------------------------|------|-----|-----|------|----|
| Static Characteristics  |                                  |                                                                                            |      |     |     |      |    |
| B <sub>V</sub> DSS      | Drain to Source Voltage          | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA                                               | 40   |     |     | V    |    |
| I <sub>DSS</sub>        | Drain to Source Leakage Current  | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 32V                                                | 1    |     |     | μA   |    |
| I <sub>GSS</sub>        | Gate to Source Leakage Current   | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 20V                                                | 100  |     |     | nA   |    |
| V <sub>GS(th)</sub>     | Gate to Source Threshold Voltage | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                 | 1.4  | 1.8 | 2.3 | V    |    |
| R <sub>DS(on)</sub>     | Drain to Source On Resistance    | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A                                               | 3.3  |     |     | 4.3  | mΩ |
|                         |                                  | V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A                                                | 2.5  |     |     | 3.2  | mΩ |
| g <sub>fs</sub>         | Transconductance                 | V <sub>DS</sub> = 20V, I <sub>D</sub> = 25A                                                | 118  |     |     | S    |    |
| Dynamic Characteristics |                                  |                                                                                            |      |     |     |      |    |
| C <sub>iss</sub>        | Input Capacitance                | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V,<br>f = 1MHz                                   | 3200 |     |     | 3840 | pF |
| C <sub>oss</sub>        | Output Capacitance               |                                                                                            | 725  |     |     | 870  | pF |
| C <sub>rss</sub>        | Reverse Transfer Capacitance     |                                                                                            | 18   |     |     | 23   | pF |
| R <sub>G</sub>          | Series Gate Resistance           |                                                                                            | 1.2  |     |     | 2.4  | Ω  |
| Q <sub>g</sub>          | Gate Charge Total (4.5V)         | V <sub>DS</sub> = 20V, I <sub>D</sub> = 25A                                                | 20   |     |     | 24   | nC |
| Q <sub>g</sub>          | Gate Charge Total (10V)          |                                                                                            | 42   |     |     | 50   |    |
| Q <sub>gd</sub>         | Gate Charge Gate to Drain        |                                                                                            | 5.9  |     |     |      | nC |
| Q <sub>gs</sub>         | Gate Charge Gate to Source       |                                                                                            | 8.1  |     |     |      | nC |
| Q <sub>g(th)</sub>      | Gate Charge at V <sub>th</sub>   |                                                                                            | 5.7  |     |     |      | nC |
| Q <sub>oss</sub>        | Output Charge                    | V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V                                                | 48   |     |     |      | nC |
| t <sub>d(on)</sub>      | Turn On Delay Time               | V <sub>DS</sub> = 20V, V <sub>GS</sub> = 10V,<br>I <sub>DS</sub> = 25A, R <sub>G</sub> = 0 | 4.7  |     |     |      | ns |
| t <sub>r</sub>          | Rise Time                        |                                                                                            | 10   |     |     |      | ns |
| t <sub>d(off)</sub>     | Turn Off Delay Time              |                                                                                            | 20   |     |     |      | ns |
| t <sub>f</sub>          | Fall Time                        |                                                                                            | 3.4  |     |     |      | ns |
| Diode Characteristics   |                                  |                                                                                            |      |     |     |      |    |
| V <sub>SD</sub>         | Diode Forward Voltage            | I <sub>DS</sub> = 25A, V <sub>GS</sub> = 0V                                                | 0.8  |     |     | 1    | V  |
| Q <sub>rr</sub>         | Reverse Recovery Charge          | V <sub>DS</sub> = 20V, I <sub>F</sub> = 25A, di/dt = 300A/μs                               | 70   |     |     |      | nC |
| t <sub>rr</sub>         | Reverse Recovery Time            |                                                                                            | 40   |     |     |      | ns |

## THERMAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

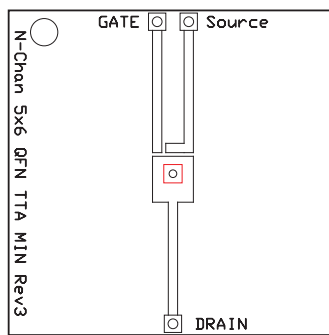
| PARAMETER        |                                                          | MIN | TYP | MAX | UNIT |
|------------------|----------------------------------------------------------|-----|-----|-----|------|
| R <sub>θJC</sub> | Thermal Resistance Junction to Case <sup>(1)</sup>       |     |     | 1   | °C/W |
| R <sub>θJA</sub> | Thermal Resistance Junction to Ambient <sup>(1)(2)</sup> |     |     | 50  | °C/W |

- (1) R<sub>θJC</sub> is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
- (2) Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.



M0137-01

Max  $R_{\theta JA} = 50^{\circ}\text{C/W}$   
when mounted on  
1 inch<sup>2</sup> (6.45-cm<sup>2</sup>) of 2-  
oz. (0.071-mm thick)  
Cu.



M0137-02

Max  $R_{\theta JA} = 122^{\circ}\text{C/W}$   
when mounted on a  
minimum pad area of  
2-oz. (0.071-mm thick)  
Cu.

## TYPICAL MOSFET CHARACTERISTICS

( $T_A = 25^{\circ}\text{C}$  unless otherwise stated)

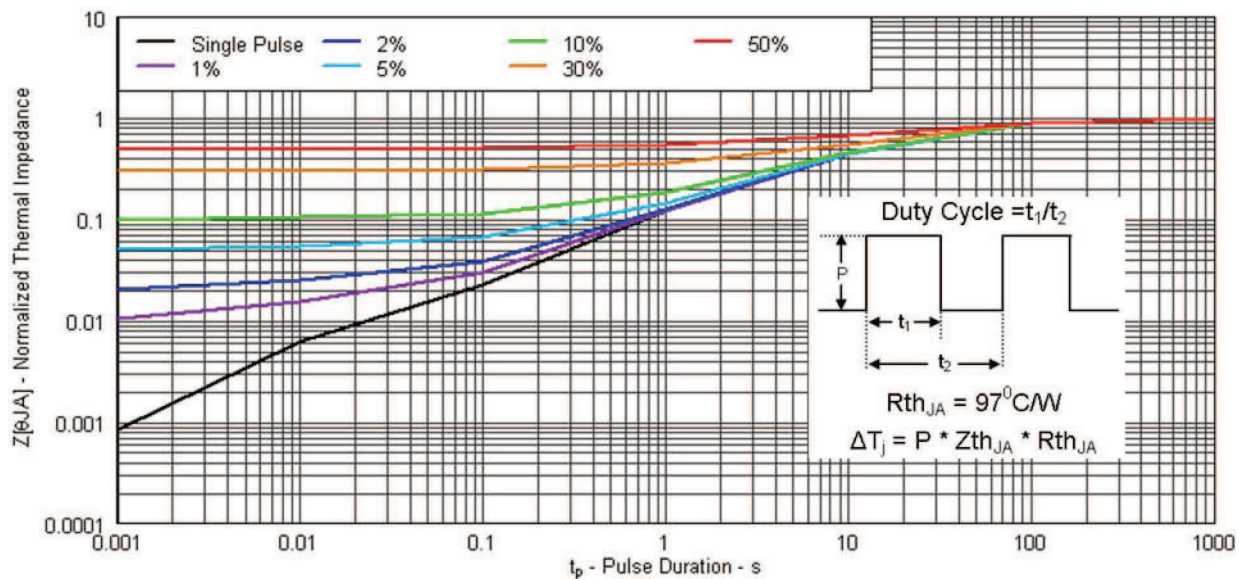


Figure 1. Transient Thermal Impedance

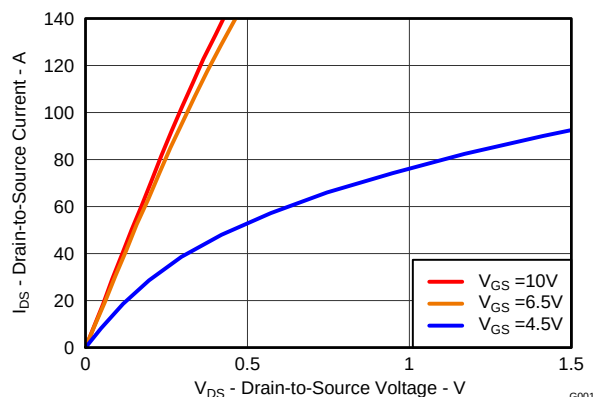


Figure 2. Saturation Characteristics

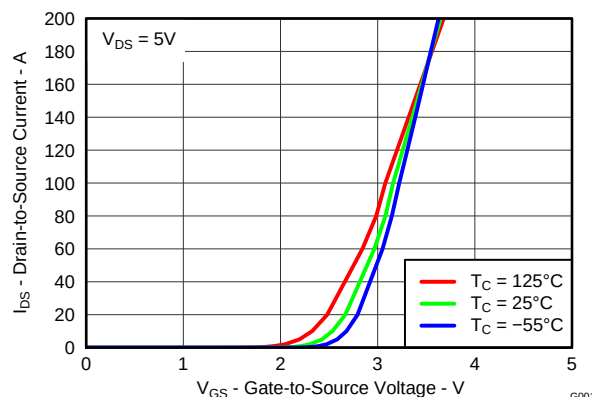


Figure 3. Transfer Characteristics

## TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

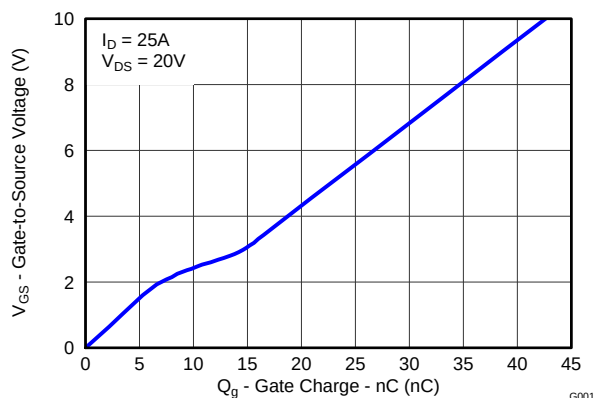


Figure 4. Gate Charge

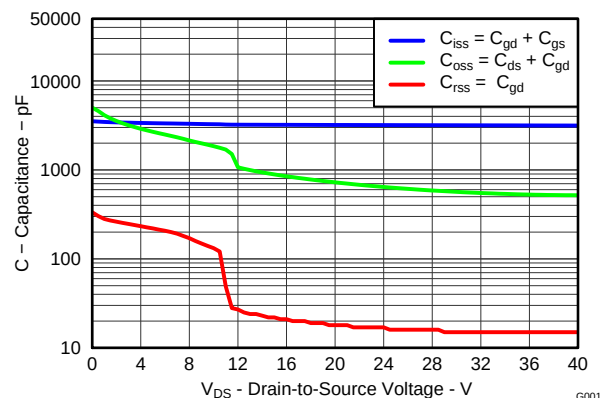


Figure 5. Capacitance

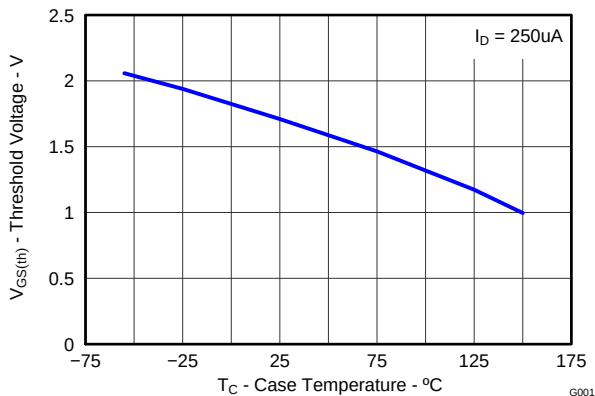


Figure 6. Threshold Voltage vs. Temperature

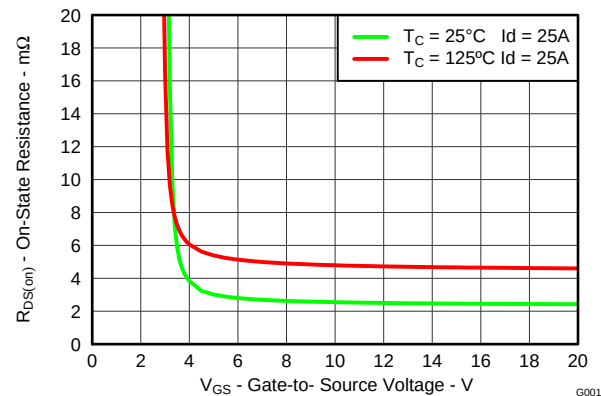


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

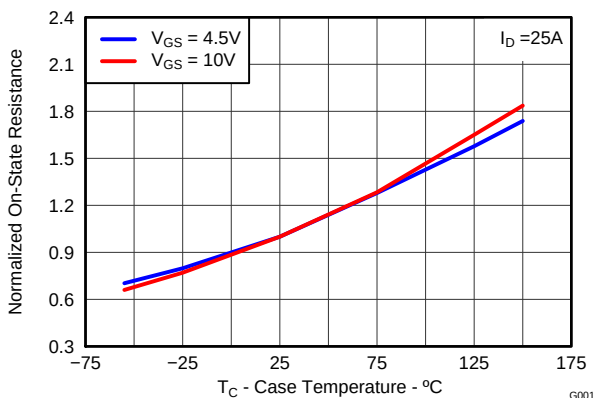


Figure 8. Normalized On-State Resistance vs. Temperature

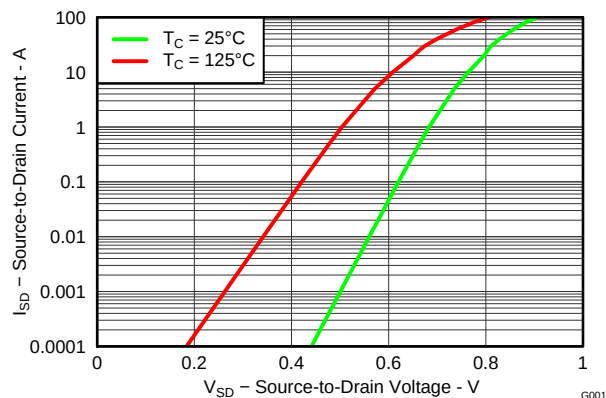


Figure 9. Typical Diode Forward Voltage

## TYPICAL MOSFET CHARACTERISTICS (continued)

( $T_A = 25^\circ\text{C}$  unless otherwise stated)

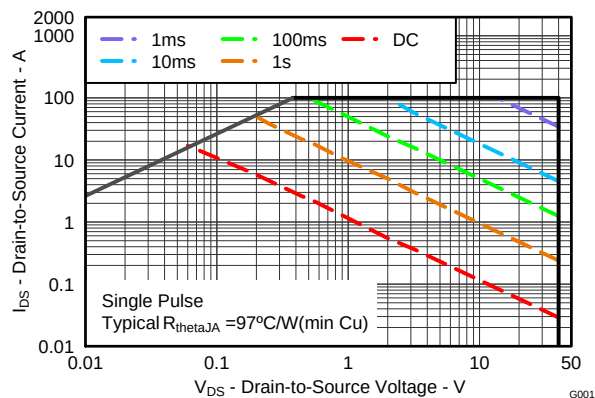


Figure 10. Maximum Safe Operating Area

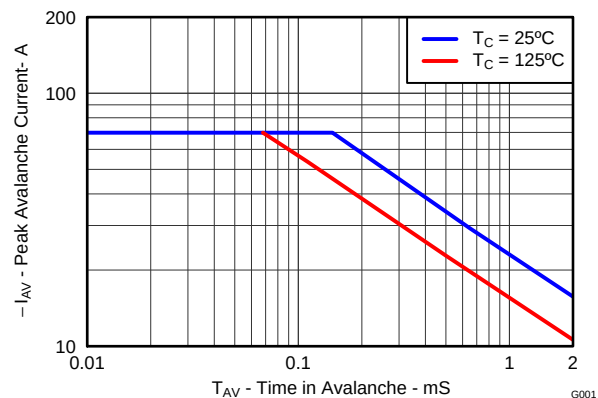


Figure 11. Single Pulse Unclamped Inductive Switching

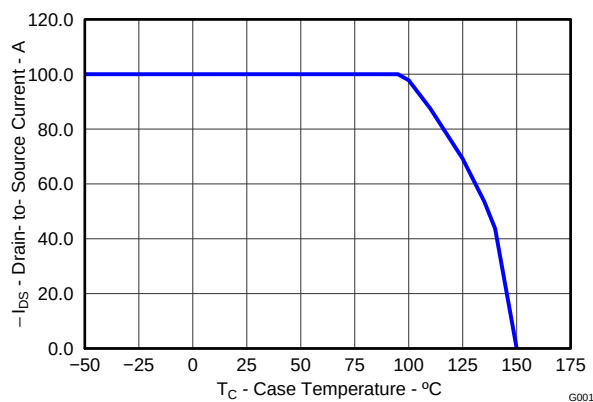
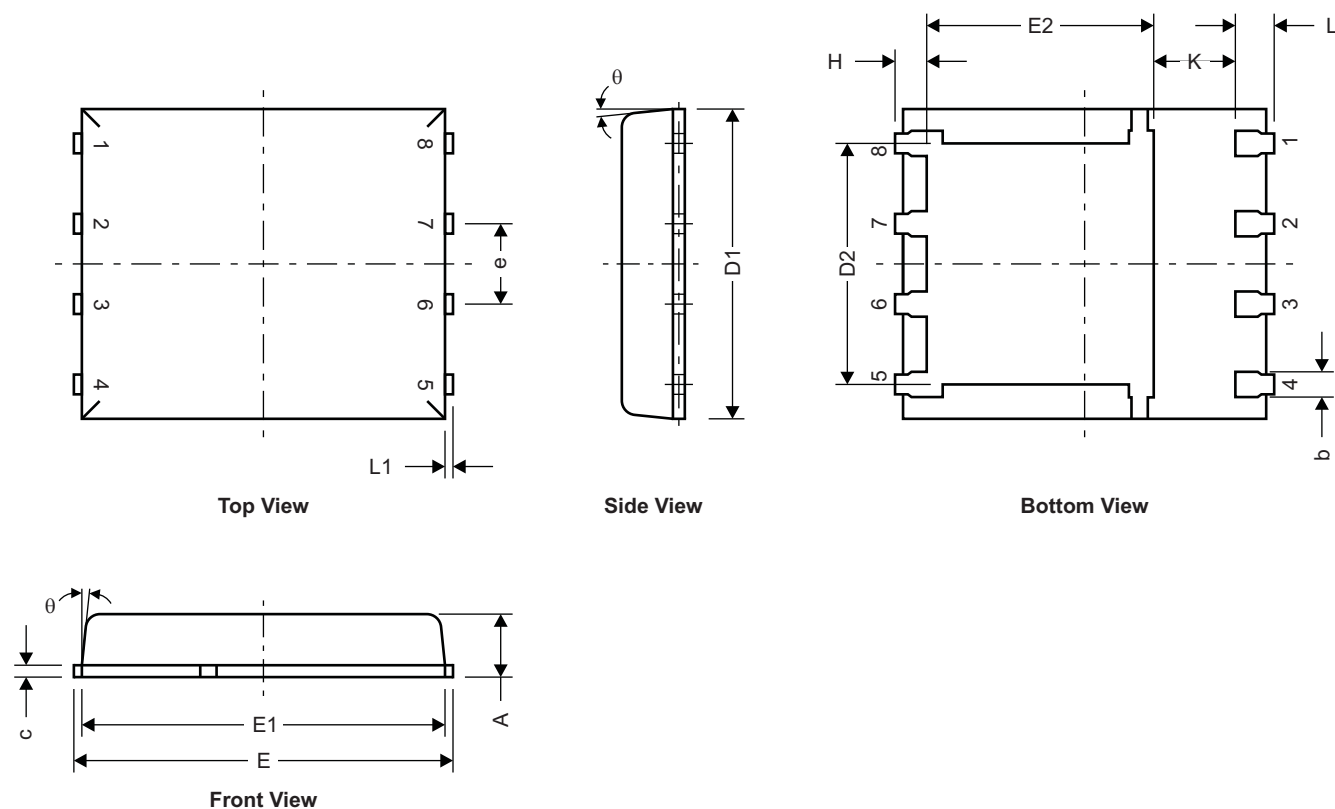


Figure 12. Maximum Drain Current vs. Temperature

## MECHANICAL DATA

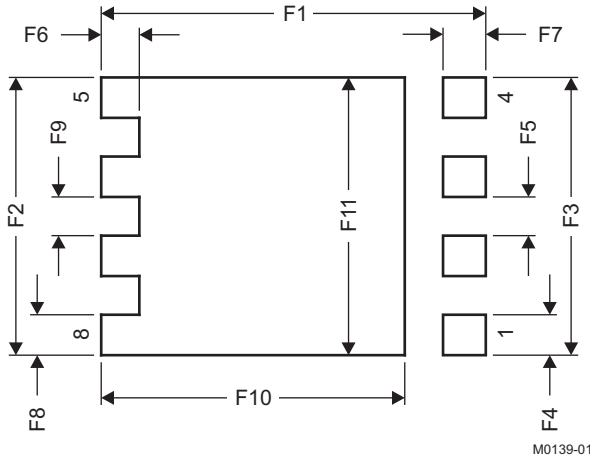
### Q5A Package Dimensions



M0135-01

| DIM      | MILLIMETERS |      |      |
|----------|-------------|------|------|
|          | MIN         | NOM  | MAX  |
| A        | 0.90        | 1.00 | 1.10 |
| b        | 0.33        | 0.41 | 0.51 |
| c        | 0.20        | 0.25 | 0.34 |
| D1       | 4.80        | 4.90 | 5.00 |
| D2       | 3.61        | 3.81 | 4.02 |
| E        | 5.90        | 6.00 | 6.10 |
| E1       | 5.70        | 5.75 | 5.80 |
| E2       | 3.38        | 3.58 | 3.78 |
| e        | 1.17        | 1.27 | 1.37 |
| H        | 0.41        | 0.56 | 0.71 |
| K        | 1.10        |      |      |
| L        | 0.51        | 0.61 | 0.71 |
| L1       | 0.06        | 0.13 | 0.20 |
| $\theta$ | 0°          |      | 12°  |

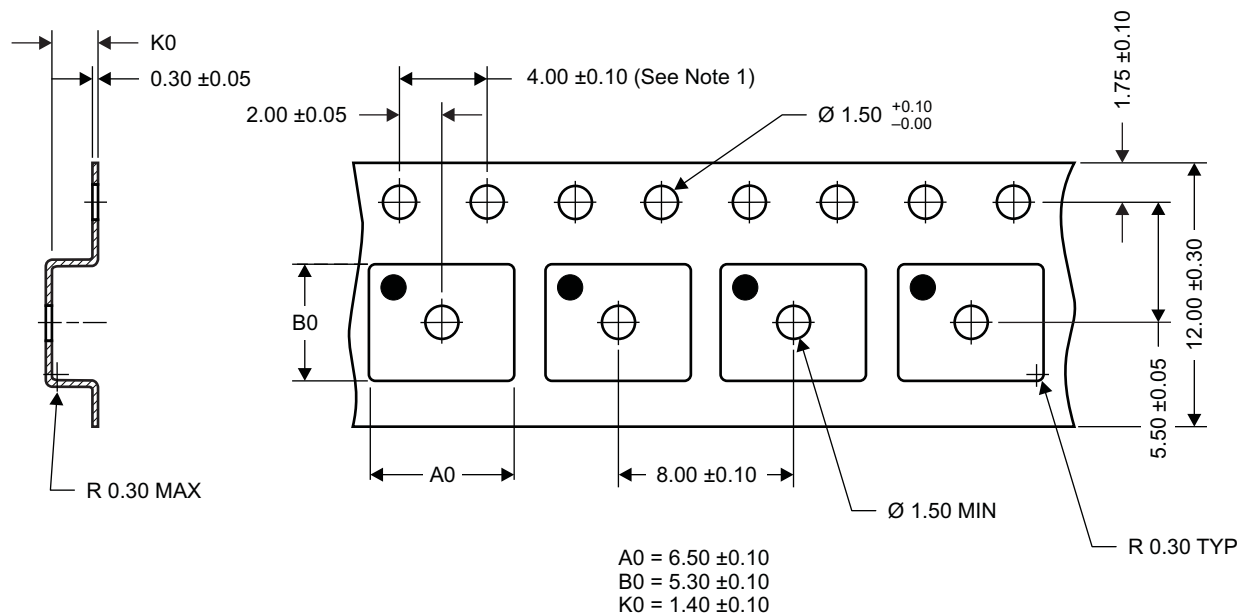
**Figure 13. Recommended PCB Pattern**



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| F1  | 6.205       | 6.305 | 0.244  | 0.248 |
| F2  | 4.46        | 4.56  | 0.176  | 0.18  |
| F3  | 4.46        | 4.56  | 0.176  | 0.18  |
| F4  | 0.65        | 0.7   | 0.026  | 0.028 |
| F5  | 0.62        | 0.67  | 0.024  | 0.026 |
| F6  | 0.63        | 0.68  | 0.025  | 0.027 |
| F7  | 0.7         | 0.8   | 0.028  | 0.031 |
| F8  | 0.65        | 0.7   | 0.026  | 0.028 |
| F9  | 0.62        | 0.67  | 0.024  | 0.026 |
| F10 | 4.9         | 5     | 0.193  | 0.197 |
| F11 | 4.46        | 4.56  | 0.176  | 0.18  |

For recommended circuit layout for PCB designs, see application note [SLPA005 – Reducing Ringing Through PCB Layout Techniques](#).

## Q5A Tape and Reel Information



### Notes:

1. 10-sprocket hole-pitch cumulative tolerance  $\pm 0.2$
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

REVISION HISTORY

| Changes from Original (June 2012) to Revision A                                                                                                                        | Page              |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|
| • Added "Typical Values at 25°C unless otherwise stated" to the Product Summary table .....                                                                            | <a href="#">1</a> |
| <hr/>                                                                                                                                                                  |                   |
| Changes from Revision A (June 2012) to Revision B                                                                                                                      | Page              |
| • Changed the Transconductance TYP value From: 142 S To: 118 S. ....                                                                                                   | <a href="#">2</a> |
| • Changed the Turn On and Turn Off Delay Time, Rise and Fall Time Test Conditions From: $I_{DS} = 25A$ , $R_G = 2\Omega$ To:<br>$I_{DS} = 25A$ , $R_G = 0\Omega$ ..... | <a href="#">2</a> |
| • Changed the $Q_{rr}$ Reverse Recovery Charge TYP value From: 21 nC To: 70 nC .....                                                                                   | <a href="#">2</a> |



**PACKAGING INFORMATION**

| Orderable Device | Status <sup>(1)</sup> | Package Type | Package Drawing | Pins | Package Qty | Eco Plan <sup>(2)</sup> | Lead/ Ball Finish | MSL Peak Temp <sup>(3)</sup> | Samples (Requires Login) |
|------------------|-----------------------|--------------|-----------------|------|-------------|-------------------------|-------------------|------------------------------|--------------------------|
| CSD18501Q5A      | ACTIVE                | SON          | DQJ             | 8    | 2500        | Pb-Free (RoHS Exempt)   | CU SN             | Level-1-260C-UNLIM           |                          |

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

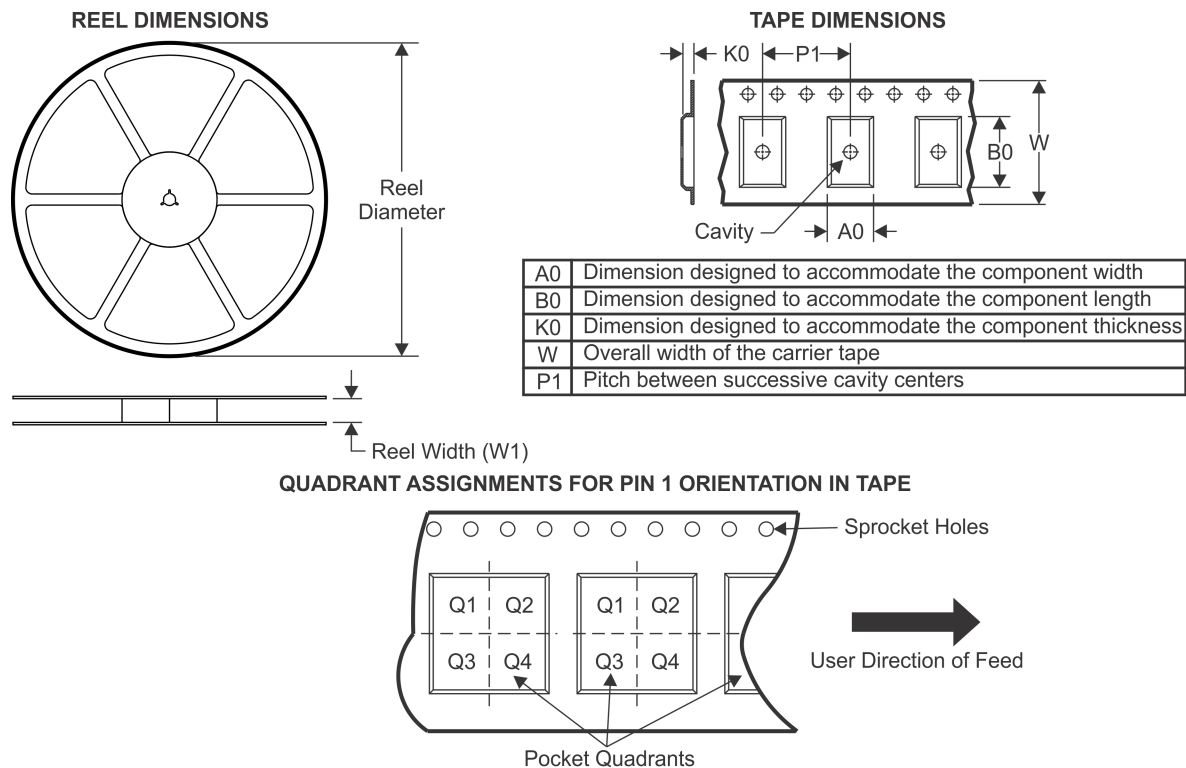
**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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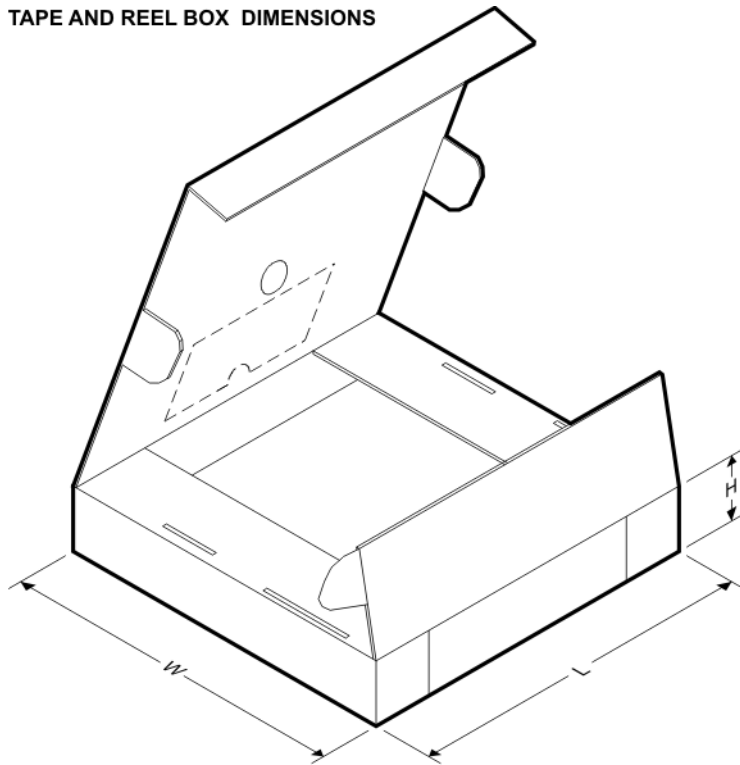
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**TAPE AND REEL INFORMATION**


\*All dimensions are nominal

| Device      | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| CSD18501Q5A | SON          | DQJ             | 8    | 2500 | 330.0              | 12.4               | 6.3     | 5.3     | 1.2     | 8.0     | 12.0   | Q1            |

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

| Device      | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|-------------|--------------|-----------------|------|------|-------------|------------|-------------|
| CSD18501Q5A | SON          | DQJ             | 8    | 2500 | 340.0       | 340.0      | 38.0        |

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### Products

|                              |                                                                                      |
|------------------------------|--------------------------------------------------------------------------------------|
| Audio                        | <a href="http://www.ti.com/audio">www.ti.com/audio</a>                               |
| Amplifiers                   | <a href="http://amplifier.ti.com">amplifier.ti.com</a>                               |
| Data Converters              | <a href="http://dataconverter.ti.com">dataconverter.ti.com</a>                       |
| DLP® Products                | <a href="http://www.dlp.com">www.dlp.com</a>                                         |
| DSP                          | <a href="http://dsp.ti.com">dsp.ti.com</a>                                           |
| Clocks and Timers            | <a href="http://www.ti.com/clocks">www.ti.com/clocks</a>                             |
| Interface                    | <a href="http://interface.ti.com">interface.ti.com</a>                               |
| Logic                        | <a href="http://logic.ti.com">logic.ti.com</a>                                       |
| Power Mgmt                   | <a href="http://power.ti.com">power.ti.com</a>                                       |
| Microcontrollers             | <a href="http://microcontroller.ti.com">microcontroller.ti.com</a>                   |
| RFID                         | <a href="http://www.ti-rfid.com">www.ti-rfid.com</a>                                 |
| OMAP Applications Processors | <a href="http://www.ti.com/omap">www.ti.com/omap</a>                                 |
| Wireless Connectivity        | <a href="http://www.ti.com/wirelessconnectivity">www.ti.com/wirelessconnectivity</a> |

### Applications

|                               |                                                                                          |
|-------------------------------|------------------------------------------------------------------------------------------|
| Automotive and Transportation | <a href="http://www.ti.com/automotive">www.ti.com/automotive</a>                         |
| Communications and Telecom    | <a href="http://www.ti.com/communications">www.ti.com/communications</a>                 |
| Computers and Peripherals     | <a href="http://www.ti.com/computers">www.ti.com/computers</a>                           |
| Consumer Electronics          | <a href="http://www.ti.com/consumer-apps">www.ti.com/consumer-apps</a>                   |
| Energy and Lighting           | <a href="http://www.ti.com/energy">www.ti.com/energy</a>                                 |
| Industrial                    | <a href="http://www.ti.com/industrial">www.ti.com/industrial</a>                         |
| Medical                       | <a href="http://www.ti.com/medical">www.ti.com/medical</a>                               |
| Security                      | <a href="http://www.ti.com/security">www.ti.com/security</a>                             |
| Space, Avionics and Defense   | <a href="http://www.ti.com/space-avionics-defense">www.ti.com/space-avionics-defense</a> |
| Video and Imaging             | <a href="http://www.ti.com/video">www.ti.com/video</a>                                   |

### TI E2E Community

[e2e.ti.com](http://e2e.ti.com)



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.